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- 1. A semiconductor device, comprising:
- a channel region located in a semiconductor substrate;
- a trench located adjacent a side of the channel region;
- an isolation structure located in the trench; and
- a source/drain region located over the isolation structure.
 - 2. The semiconductor device as recited in Claim 1 wherein the trench is a first trench and the semiconductor device further includes a second trench located on an opposing side of the channel region, wherein the isolation structure is a first isolation structure located in the first trench and the semiconductor device further includes a second isolation structure located in the second trench, and wherein the source/drain region is a first source/drain region and the semiconductor device further includes a second source/drain region located over the second isolation structure.
 - 3. The semiconductor device as recited in Claim 1 wherein the source/drain region comprises polysilicon.
- 4. The semiconductor devices as recited in Claim 1 wherein the source/drain region comprises epitaxial silicon.

- The semiconductor device as recited in Claim 1 wherein a 5. side wall of the trench includes an oxide layer. 2
- The semiconductor device as recited in Claim 5 further 2 including a nitrided layer located on the oxide layer.
- The distriction and the second of the second The semiconductor device as recited in Claim 1 wherein 7. the isolation structure comprises an oxide.
 - The semiconductor device as recited in Claim 1 wherein 8. the source/drain region includes a lightly doped source/drain region having a dopant concentration ranging from about 1E16 atoms/cm³ to about 1E17 atoms/cm³, and a source/drain contact region having a dopant concentration up to about 1E22 atoms/cm3.

- 9. A method of manufacturing a semiconductor device, comprising:
- forming a channel region in a semiconductor substrate;
- 4 forming a trench adjacent a side of the channel region;
- forming an isolation structure in the trench; and

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- forming a source/drain region over the isolation structure.
 - 10. The method as recited in Claim 9 wherein forming the trench includes forming a first trench and the method further includes forming a second trench on an opposing side of the channel region, wherein forming the isolation structure includes forming a first isolation structure in the first trench and the method further includes forming a second isolation structure in the second trench, and wherein forming the source/drain region includes forming a first source/drain region and the method further includes forming a second source/drain region over the second isolation structure.
 - 11. The method as recited in Claim 9 wherein forming the source/drain region includes forming a polysilicon source/drain region.
 - 12. The methods as recited in Claim 9 wherein forming the

- source/drain region includes epitaxially growing the source/drain region from the channel region.
- 13. The method as recited in Claim 9 further including2 forming an oxide layer on a side wall of the trench.
 - 14. The method as recited in Claim 13 further including forming a nitrided layer on the oxide layer.
 - 15. The method as recited in Claim 9 wherein forming an isolation structure includes forming an isolation structure comprising an oxide.

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16. The method as recited in Claim 9 wherein forming a source/drain region includes forming a lightly doped source/drain region having a dopant concentration ranging from about 1E16 atoms/cm³ to about 1E17 atoms/cm³, and forming a source/drain contact region having a dopant concentration up to about 1E22 atoms/cm³.

- 17. An integrated circuit, comprising:
- 2 semiconductor devices, including;

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- a channel region located in a semiconductor substrate;
- a trench located adjacent a side of the channel region;
- an isolation structure located in the trench; and
- a source/drain region located over the isolation structure; and

dielectric layers located over the semiconductor devices and having interconnect structures located therein that electrically connect the semiconductor devices to form an operative-integrated circuit.

- 18. The integrated circuit as recited in Claim 17 wherein the trench is a first trench and the semiconductor device further includes a second trench located on an opposing side of the channel region, wherein the isolation structure is a first isolation structure located in the first trench and the semiconductor device further includes a second isolation structure located in the second trench, and wherein the source/drain region is a first source/drain region and the semiconductor device further includes a second source/drain region located over the second isolation structure.
 - 19. The integrated circuit as recited in Claim 17 wherein the

- 2 isolation structure comprises an oxide.
- 20. The integrated circuit as recited in Claim 17 wherein the 2 semiconductor devices form part of an N-type metal oxide 3 semiconductor (NMOS) device, a P-type metal oxide semiconductor 4 (PMOS) device, a complementary metal oxide semiconductor (CMOS)

device, a bipolar device, or a memory device.